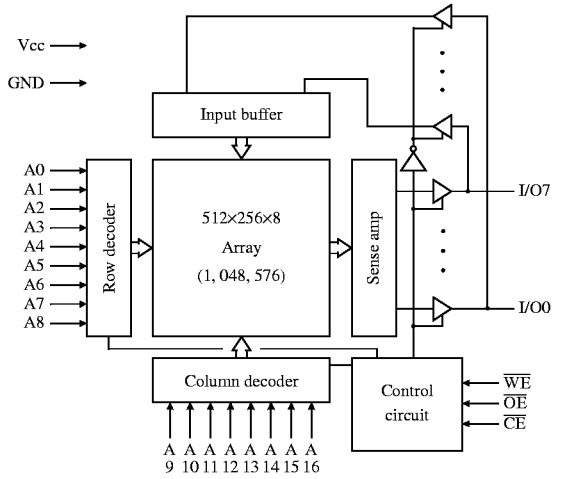
5V/3.3V 128K×8 CMOS SRAM (Common I/O)

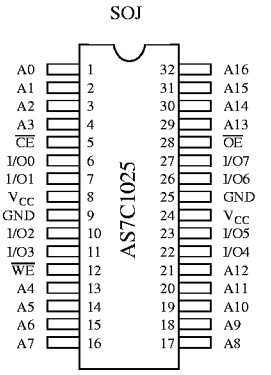
Features

- Organization: 131,072 words × 8 bits
- High speed
  - 10/12/15/20 ns address access time
  - 3/3/4/5 ns output enable access time
- Low power consumption
  - Active: 770 mW max (10 ns cycle, 5V)
  - Standby: 27.5 mW max, CMOS I/O (5V)
  - Very low DC component in active power
- 2.0V data retention
- Equal access and cycle times
- Easy memory expansion with $\overline{CE}$, $\overline{OE}$ inputs
- TTL-compatible, three-state I/O
- 32-pin JEDEC standard package
  - 300/400 mil SOJ
- Center power and ground pins for low noise
- ESD protection ≥ 2000 volts
- Latch-up current ≥ 200 mA
- 3.3V version available (AS7C31025)
- Industrial and commercial temperature available

Logic block diagram



Pin arrangement



Selection guide

		7C1025-10 —	7C1025-12 7C31025-12	7C1025-15 7C31025-15	7C1025-20 7C31025-20	Unit
Maximum address access time		10	12	15	20	ns
Maximum output enable access time		3	3	4	5	ns
Maximum operating current	AS7C1025	140	130	120	110	mA
	AS7C31025	–	100	85	80	mA
Maximum CMOS standby current		5	5	5	5	mA

Shaded areas contain advance information.

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Functional description

The AS7C1025 and AS7C31025 are high performance CMOS 1,048,576-bit Static Random Access Memories (SRAM) organized as 131,072 words × 8 bits. They are designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA}, t_{RC}, t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 3/3/4/5 ns are ideal for high performance applications. The chip enable input $\overline{CE}$ permits easy memory expansion with multiple-bank memory systems.

When $\overline{CE}$ is HIGH the device enters standby mode. The standard AS7C1025 is guaranteed not to exceed 27.5 mW power consumption in standby mode, and typically requires only 5 mW. Both devices also offer 2.0V data retention.

A write cycle is accomplished by asserting write enable ($\overline{WE}$) and chip enable ($\overline{CE}$). Data on the input pins I/O0-I/O7 is written on the rising edge of $\overline{WE}$ (write cycle 1) or $\overline{CE}$ (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ($\overline{OE}$) or write enable ($\overline{WE}$).

A read cycle is accomplished by asserting output enable ($\overline{OE}$) and chip enable ($\overline{CE}$), with write enable ($\overline{WE}$) HIGH. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible, and operation is from a single 5V supply (AS7C1025) or 3.3V supply (7C31025). The AS7C1025 and AS7C31025 are packaged in common industry standard packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Voltage on any pin relative to GND	V_t	–0.5	+7.0	V
Power dissipation	P_D	–	1.0	W
Storage temperature (plastic)	T_{stg}	–55	+150	°C
DC output current	I_{out}	–	20	mA

Stresses greater than those listed under **Absolute Maximum Ratings** may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Data	Mode
H	X	X	High Z	Standby (I_{SB}, I_{SB1})
L	H	H	High Z	Output disable
L	H	L	D_{out}	Read
L	L	X	D_{in}	Write

Key: X = Don't Care, L = LOW, H = HIGH

Recommended operating conditions

Parameter		Symbol	Min	Nominal	Max	Unit
Supply voltage	AS7C1025	V_{CC}	4.5	5.0	5.5	V
	AS7C31025	V_{CC}	3.0	3.3	3.6	V
		GND	0.0	0.0	0.0	V
Input voltage	AS7C1025	V_{IH}	2.2	–	V_{CC} + 0.5	V
	AS7C31025	V_{IH}	2.0	–	V_{CC} + 0.5	V
		V_{IL}	–0.5	–	0.8	V
Ambient operating temperature		T_A	0	–	70	℃

V_{IL} min = –3.0V for pulse width less than $t_{RC}/2$.

DC operating characteristics

Parameter	Symbol	Test conditions		-10 Min	-10 Max	-12 Min	-12 Max	-15 Min	-15 Max	-20 Min	-20 Max	Unit
Input leakage current	$\lvert I_{LI} \rvert$	V_{CC} = Max, V_{in} = GND to V_{CC}		–	2	–	2	–	2	–	2	µA
Output leakage current	$\lvert I_{LO} \rvert$	$\overline{CE1}$ = V_{IH}, V_{CC} = Max, V_{out} = GND to V_{CC}		–	5	–	5	–	5	–	5	µA
Operating power supply current	I_{CC}	$\overline{CE1}$ = V_{IL}, f = f_{max}, I_{out} = 0 mA	AS7C1025	–	140	–	130	–	120	–	110	mA
			AS7C31025	–	135	–	100	–	85	–	80	mA
Standby power supply current [1]	I_{SB}	$\overline{CE1}$ = V_{IH}, f = f_{max}		–	55	–	50	–	40	–	40	mA
	I_{SB1}	$\overline{CE1} \geq V_{CC}$–0.2V, $V_{in} \leq$ 0.2V or $V_{in} \geq V_{CC}$–0.2V, f = 0		–	5	–	5	–	5	–	5	mA
Output voltage	V_{OL}	I_{OL} = 8 mA, V_{CC} = Min		–	0.4	–	0.4	–	0.4	–	0.4	V
	V_{OH}	I_{OH} = –4 mA, V_{CC} = Min		2.4	–	2.4	–	2.4	–	2.4	–	V

Shaded areas contain advance information.

Capacitance [2]

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C_{IN}	A, $\overline{CE}$, $\overline{WE}$, $\overline{OE}$	V_{in} = 0V	5	pF
I/O capacitance	$C_{I/O}$	I/O	V_{in} = V_{out} = 0V	7	pF

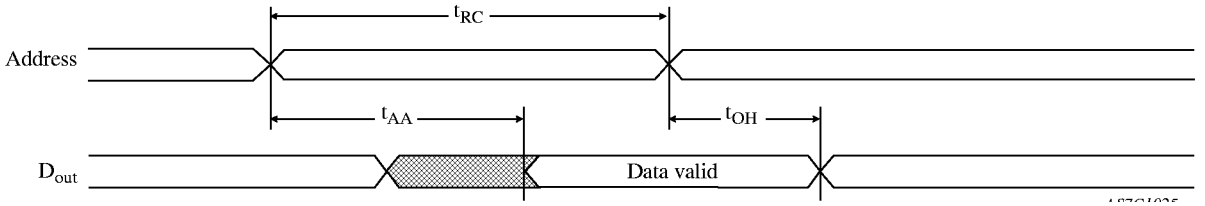
Read cycle [3, 9]

		-10		-12		-15		-20			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t_{RC}	10	–	12	–	15	–	20	–	ns	
Address access time	t_{AA}	–	10	–	12	–	15	–	20	ns	3
Chip enable ($\overline{CE}$) access time	t_{ACE}	–	10	–	12	–	15	–	20	ns	3
Output enable ($\overline{OE}$) access time	t_{OE}	–	3	–	3	–	4	–	5	ns	
Output hold from address change	t_{OH}	2	–	3	–	3	–	3	–	ns	5
$\overline{CE}$ LOW to output in low Z	t_{CLZ}	0	–	0	–	0	–	0	–	ns	4, 5
$\overline{CE}$ HIGH to output in high Z	t_{CHZ}	–	3	–	3	–	4	–	5	ns	4, 5
$\overline{OE}$ LOW to output in low Z	t_{OLZ}	0	–	0	–	0	–	0	–	ns	4, 5
$\overline{OE}$ HIGH to output in high Z	t_{OHZ}	–	3	–	3	–	4	–	5	ns	4, 5
Power up time	t_{PU}	0	–	0	–	0	–	0	–	ns	4, 5
Power down time	t_{PD}	–	10	–	12	–	15	–	20	ns	4, 5

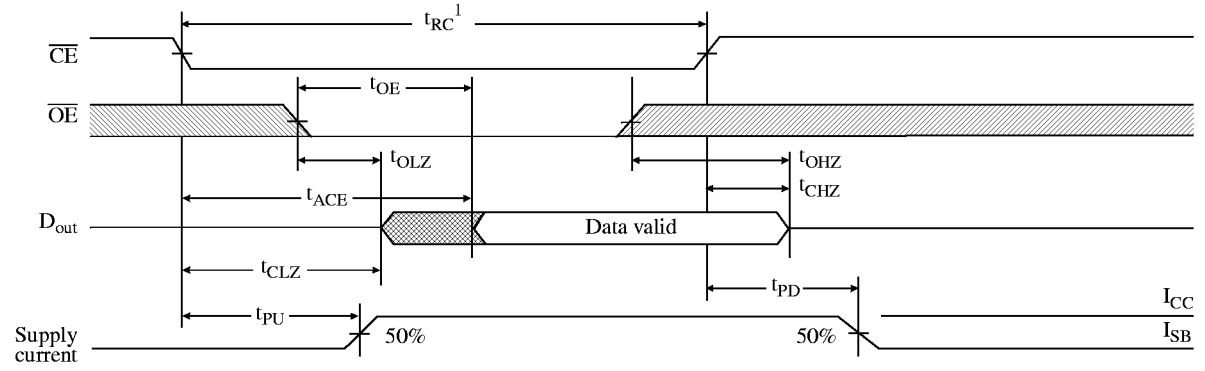
Key to switching waveforms

Rising input Falling input Undefined output/don't care

Read waveform 1 [3, 6, 7, 9]



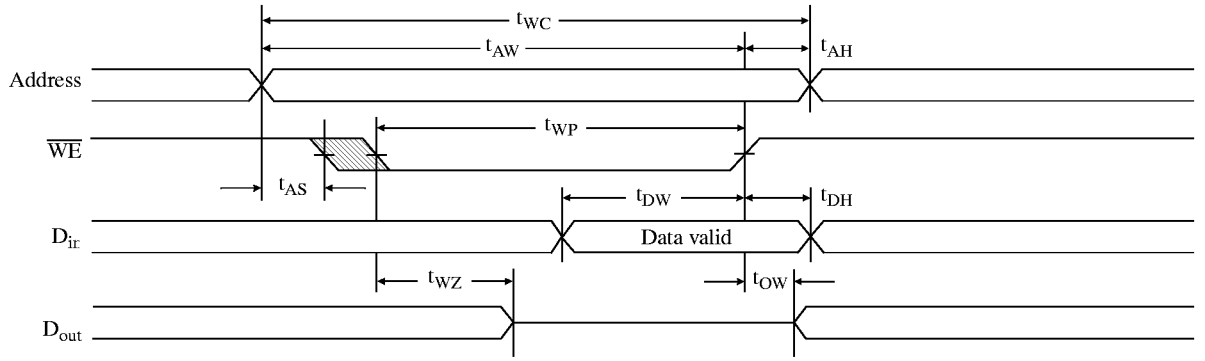
Read waveform 2 [3, 6, 8, 9]



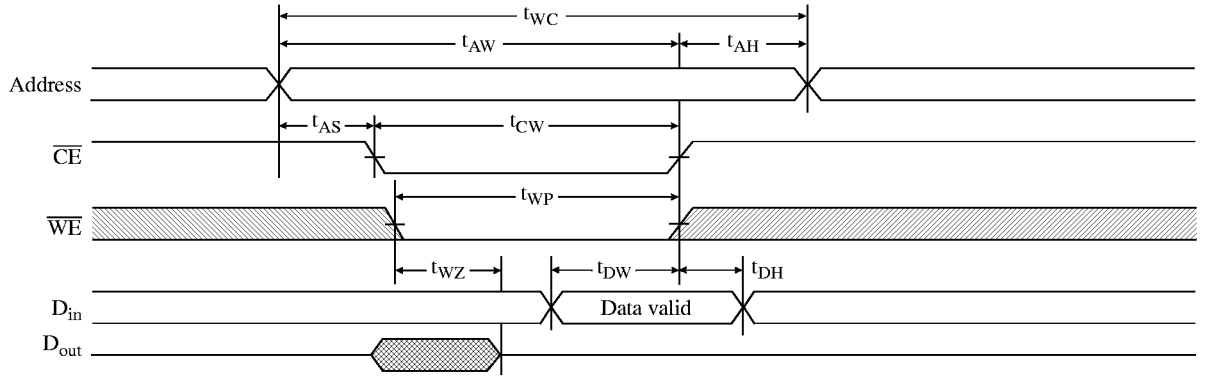
Write cycle [11]

		-10		-12		-15		-20			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write cycle time	t_{WC}	10	–	12	–	15	–	20	–	ns	
Chip enable ($\overline{CE}$) to write end	t_{CW}	9	–	10	–	12	–	12	–	ns	
Address setup to write end	t_{AW}	9	–	10	–	12	–	12	–	ns	
Address setup time	t_{AS}	0	–	0	–	0	–	0	–	ns	
Write pulse width	t_{WP}	7	–	8	–	9	–	12	–	ns	
Address hold from end of write	t_{AH}	0	–	0	–	0	–	0	–	ns	
Data valid to write end	t_{DW}	6	–	6	–	8	–	10	–	ns	
Data hold time	t_{DH}	0	–	0	–	0	–	0	–	ns	4, 5
Write enable to output in high Z	t_{WZ}	–	5	–	5	–	5	–	5	ns	4, 5
Output active from write end	t_{OW}	3	–	3	–	3	–	3	–	ns	4, 5

Write waveform 1 [10, 11]



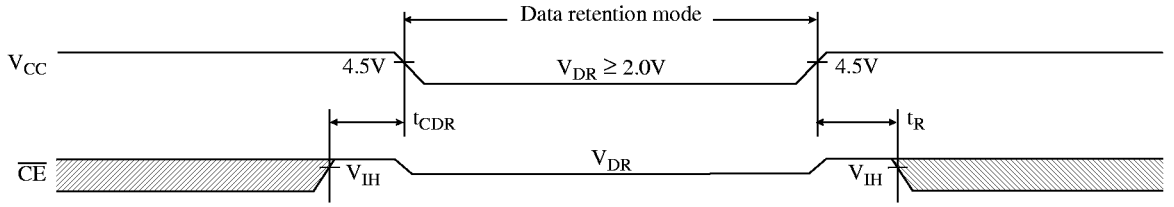
Write waveform 2 [10, 11]



Data retention characteristics

Parameter	Symbol	Test conditions	Min	Max	Unit
V_{CC} for data retention	V_{DR}	V_{CC} = 2.0V $\overline{CE} \geq V_{CC}-0.2V$ $V_{in} \geq V_{CC}-0.2V$ or $V_{in} \leq 0.2V$	2.0	–	V
Data retention current	I_{CCDR}		–	500	µA
Chip enable to data retention time	t_{CDR}		0	–	ns
Operation recovery time	t_R		t_{RC}	–	ns
Input leakage current	$\lvert I_{LI} \rvert$		–	1	µA

Data retention waveform



AC test conditions

- Output load: see Figure B, except as noted.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 5 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

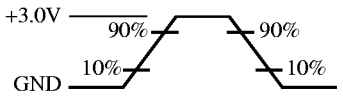


Figure A: Input waveform

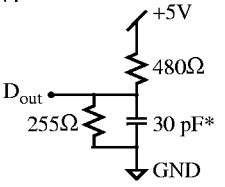


Figure B: Output load

Thevenin equivalent:

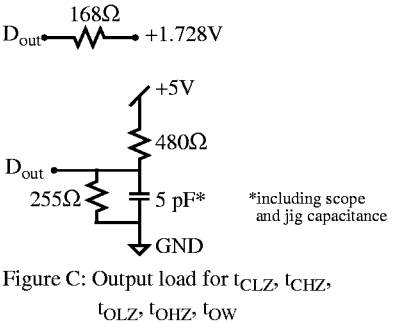


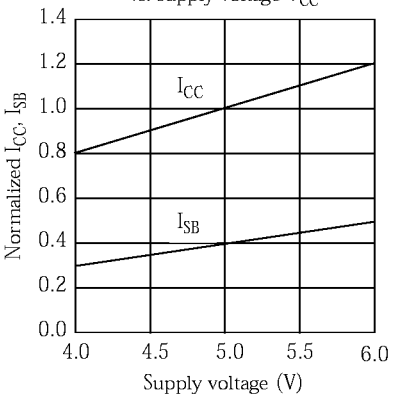
Figure C: Output load for t_{CLZ}, t_{CHZ}, t_{OLZ}, t_{OHZ}, t_{OW}

Notes

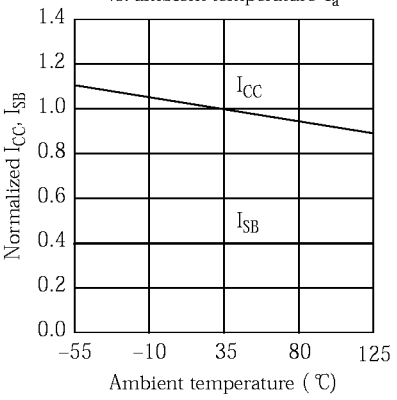
1 During V_{CC} power-up, a pull-up resistor to V_{CC} on $\overline{CE}$ is required to meet I_{SB} specification.
2 This parameter is sampled and not 100% tested.
3 For test conditions, see AC test conditions, Figures A, B, C.
4 t_{CLZ} and t_{CHZ} are specified with CL = 5pF as in Figure C. Transition is measured ±500mV from steady-state voltage.
5 This parameter is guaranteed but not tested.
6 $\overline{WE}$ is HIGH for read cycle.
7 $\overline{CE}$ and $\overline{OE}$ are LOW for read cycle.
8 Address valid prior to or coincident with $\overline{CE}$ transition LOW.
9 All read cycle timings are referenced from the last valid address to the first transitioning address.
10 $\overline{CE}$ or $\overline{WE}$ must be HIGH during address transitions.
11 All write cycle timings are referenced from the last valid address to the first transitioning address.
12 This data applicable to the AS7C1025. The 7C31025 functions similarly.

Typical DC and AC characteristics [12]

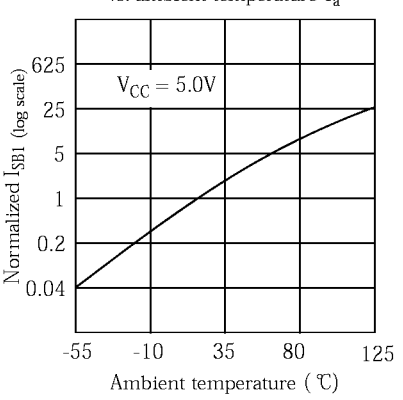
Normalized supply current I_{CC}, I_{SB} vs. supply voltage V_{CC}



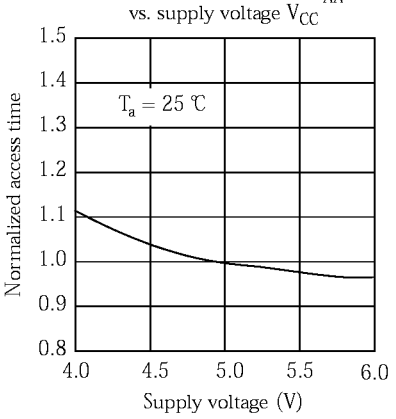
Normalized supply current I_{CC}, I_{SB} vs. ambient temperature T_a



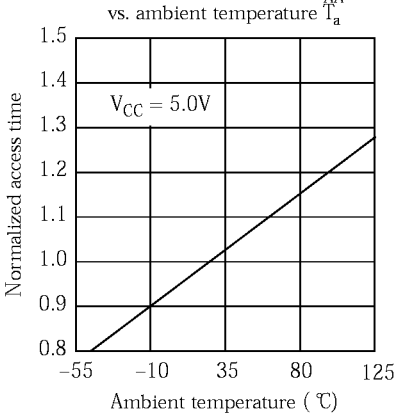
Normalized supply current I_{SB1} vs. ambient temperature T_a



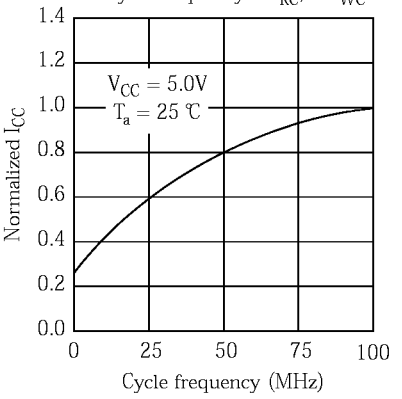
Normalized access time t_{AA} vs. supply voltage V_{CC}



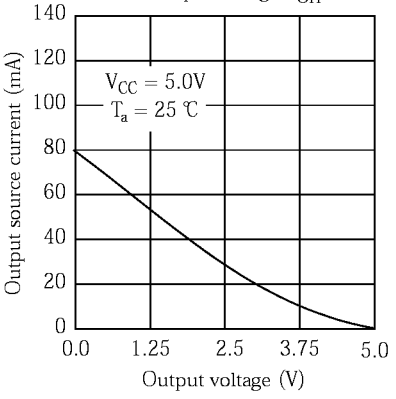
Normalized access time t_{AA} vs. ambient temperature T_a



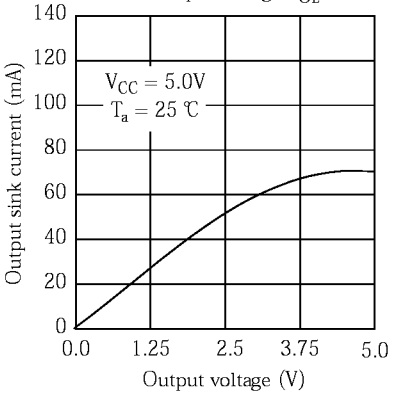
Normalized supply current I_{CC} vs. cycle frequency $1/t_{RC}$, $1/t_{WC}$



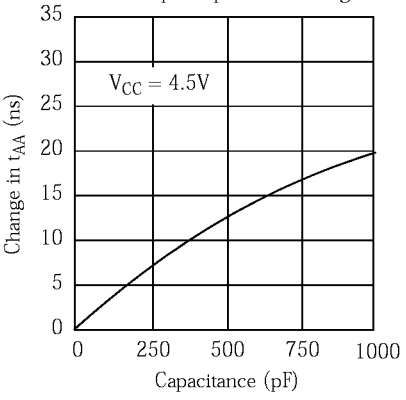
Output source current I_{OH} vs. output voltage V_{OH}



Output sink current I_{OL} vs. output voltage V_{OL}



Typical access time change Δt_{AA} vs. output capacitive loading



AS7C1025 ordering codes

Package \ Access time		10 ns	12 ns	15 ns	20 ns
Plastic SOJ, 400 mil	5V	AS7C1025-10JC	AS7C1025-12JC	AS7C1025-15JC	AS7C1025-20JC
	3.3V	AS7C31025-10JC	AS7C31025-12JC	AS7C31025-15JC	AS7C31025-20JC
			AS7C31025-12JI	AS7C31025-15JI	AS7C31025-20JI
Plastic SOJ, 300 mil	5V		AS7C1025-12TJC	AS7C1025-15TJC	
	3.3V		AS7C31025-12TJC	AS7C31025-15TJC	AS7C31025-20TJC

Shaded areas may contain advance information.

AS7C1025 part numbering system

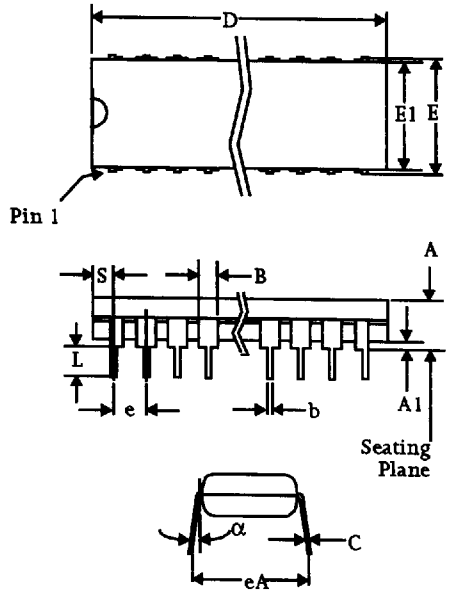
AS7C	X		1025	–XX	X		C
SRAM prefix	Blank 3	= 5V CMOS = 3.3V CMOS	Device number	Access time	Package: J = TJ =	SOJ 400 mil SOJ 300 mil	Temperature range C = Commercial, 0 ℃ to 70 ℃ I = Industrial, -40 ℃ to +85 ℃

Package diagrams

Plastic dual in-line package (PDIP)

	20-pin 300 mil		28-pin 300 mil		32-pin 300 mil		32-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.175	-	0.175	-	0.180	-	0.200
A1	0.010	-	0.010	-	0.015	-	0.015	-
B	0.046	0.054	0.058	0.064	0.045	0.055	0.045	0.065
b	0.018	0.024	0.016	0.022	0.015	0.021	0.014	0.022
C	0.008	0.014	0.008	0.014	0.008	0.012	0.009	0.015
D	-	0.980	-	1.400	-	1.571	-	1.620
E	0.290	0.310	0.295	0.320	0.300	0.325	0.390	0.425
E1	0.263	0.293	0.278	0.298	0.280	0.295	0.340	0.390
e	0.100 BSC		0.100 BSC		0.100 BSC		0.100 BSC	
eA	0.310	0.350	0.330	0.370	0.330	0.370	0.430	0.470
L	0.110	0.130	0.120	0.140	0.110	0.142	0.118	0.162
α	0°	15°	0°	15°	0°	15°	0°	15°
S	-	0.040	-	0.055	-	0.043	-	0.065

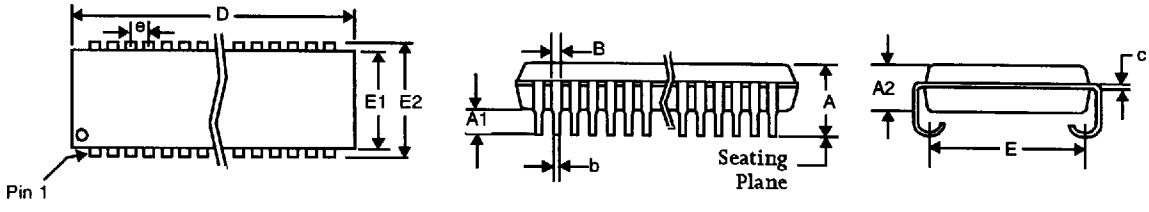
Dimensions in inches



Plastic small outline J-bend (SOJ)

	20/26-pin 300 mil		28-pin 300 mil		32-pin 300 mil		28-pin 400 mil		32-pin 400 mil		36-pin 400 mil		40-pin 400 mil		42-pin 400 mil		44-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.140	-	0.140	-	0.145	0.132	0.146	-	0.145	-	-	-	0.145	0.128	0.148	0.128	0.148
A1	0.020	-	0.025	-	0.025	-	0.062	-	0.025	-	-	-	0.025	-	0.025	-	0.025	-
A2	0.095	0.105	0.095	0.105	0.086	0.105	0.105	115	0.086	0.115	0.102 NOM		0.086	0.115	1.105	1.115	1.105	1.115
B	0.025	0.032	0.028 TYP		0.026	0.032	0.024	0.032	0.026	0.032	-	0.032	0.026	0.032	0.026	0.032	0.026	0.032
b	0.016	0.022	0.018 TYP		0.014	0.020	0.013	0.021	0.015	0.020	0.013	0.021	0.015	0.022	0.015	0.020	0.015	0.020
c	0.008	0.014	0.010 TYP		0.006	0.013	0.005	0.012	0.007	0.013	-	-	0.007	0.014	0.007	0.013	0.007	0.013
D	-	0.686	-	0.730	0.820	0.830	0.720	0.729	0.820	0.830	0.920	0.930	1.015	1.035	1.070	1.080	1.120	1.130
E	0.327	0.347	0.327	0.347	0.330	0.340	0.430	0.440	0.435	0.445	0.350	0.390	0.435	0.445	0.370 NOM		0.370 NOM	
E1	0.295	0.305	0.295	0.305	0.292	0.305	0.395	0.405	0.395	0.405	0.400 NOM		0.395	0.405	0.395	0.405	0.395	0.405
E2	0.245	0.285	0.245	0.285	0.250	0.275	0.354	0.378	0.360	0.380	0.435	0.445	0.348	0.390	0.435	0.445	0.435	0.445
e	0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.045	0.055	0.050 BSC		0.050 NOM		0.050 NOM	

Dimensions in inches



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